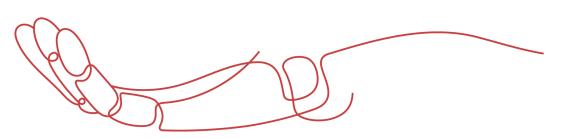




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

urces Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

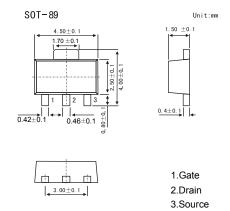


P-Channel MOSFET

■ Features

- V_{DS (V)} =-60V
- ID =-1.5 A
- ullet RDS(ON) < 1 Ω (VGS =-10V)
- RDS(ON) $< 1.5 \Omega$ (VGS =-4V)
- Comp;ementary to 2SK1483





■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	VDS	-60	V	
Gate-Source Voltage	Vgs	±20		
Continuous Drain Current	ΙD	1.5	Α	
Pulsed Drain Current (Note.1)	Ідм	3		
Power Dissipation	Po	2	W	
Junction Temperature	TJ	150	$^{\circ}$ C	
Junction Storage Temperature Range	Tstg	-55 to 150		

Note.1: PW \leq 10ms, Duty Cycle \leq 50%

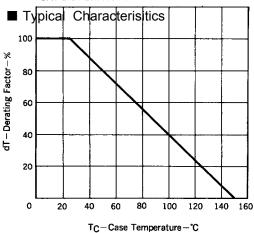
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	VDSS	ID=-250 µ A, Vgs=0V	-60			V	
Zero Gate Voltage Drain Current	IDSS	V _D s=-60V, V _G s=0V			-10	uA	
Gate-Body leakage current	Igss	V _{DS} =0V, V _{GS} = \pm 20V			±10	uA	
Gate Cut off Voltage	VGS(off)	V _D S=-10V,I _D =-1mA	-1		-3	V	
Static Drain-Source On-Resistance	RDS(On)	Vgs=-10V, ID=-0.5A			1.5	Ω	
		Vgs=-4V, ID=-0.5A			1	Ω	
Forward Transconductance	gFS	Vgs=-10V, ID=-0.5A	0.4	1		S	
Input Capacitance	Ciss			220		pF	
Output Capacitance	Coss	Vgs=0V, Vps=-10V, f=1MHz		125			
Reverse Transfer Capacitance	Crss			17			
Turn-On DelayTime	td(on)			45		ns	
Turn-On Rise Time	tr	V _{GS} (on)=-10V, V _{DS} =-25V, I _D =-0.5A,		70			
Turn-Off DelayTime	td(off)	RL=50 Ω ,RGEN=10 Ω		380			
Turn-Off Fall Time	tf			170			

-100



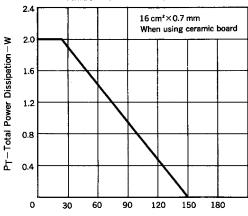




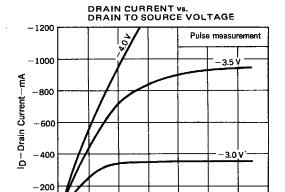
FORWARD BIAS SAFE OPERATING AREA D(pulse) 1D(DC) ID-Drain Current-A -0.3 -0.03 Ta=25 °C Single pulse -0.01

VDS-Drain to Source Voltage-V

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



Ta-Ambient Temperature-°C



0

-2.0 VDS-Drain to Source Voltage-V

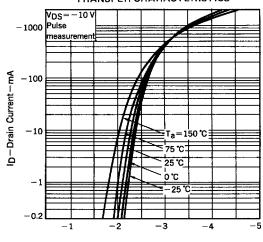
-3.0

-2.5

- 1.5

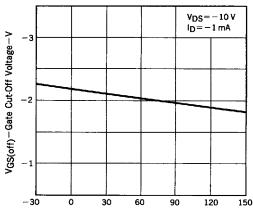
- 1.0

TRANSFER CHARACTERISTICS



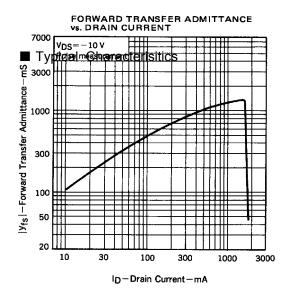
VGS-Gate to Source Voltage-V

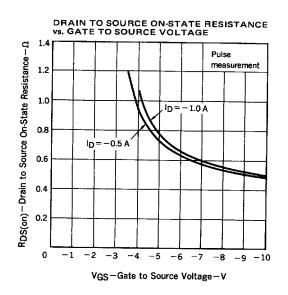
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

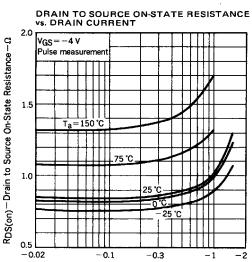


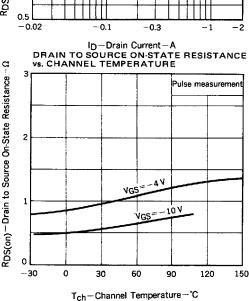
T_{ch}-Channel Temperature-°C

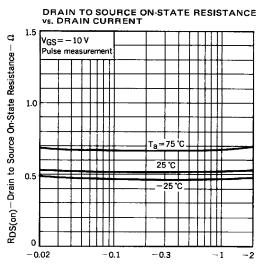


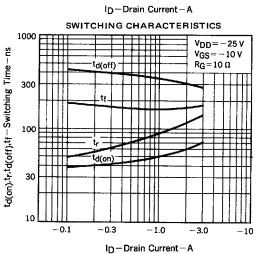






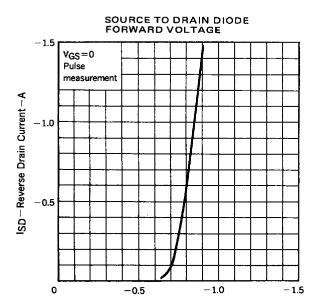








■ Typical Characterisitics



VSD-Source to Drain Voltage-V



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